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## NFORMATION DISCLOSURE STATEMENT BY APPLICANT

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Sheet 2 of 3

Complete if Known				
Application Number	09/753,256			
Filing Date	December 28, 2000/			
First Named Inventor	Valery M. Dubin			
Art Unit	2813			
Examiner Name	Nguyen, Tuan M.			
Attorney Docket Number	42390P1025			

		OTHER ART - NON PATENT LITERATURE DOCUMENTS	
Examiner Initials*	Cite No.¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T²
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TN TN		Georgiou, et al., "Thick Selective Electroless-Plated Cobalt-Nickel Alloy Contacts to CoSi <sub>2</sub> ," J. Electrochem. Soc., Vol. 138, No. 7, pp. 2061-2069 (July 1991).	
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W		Shacham-Diamand, "100 nm Wide Copper Lines Made by Selective Electroless Deposition," J. Micromech. Microeng., pp. 66-72 (1991).	

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Complete if Known tute for form 1449A/PTO Application Number 09/753,256 INFORMATION DISCLOSURE December 28, 2000 Filing Date Valery M. Dubin First Named Inventor STATEMENT BY APPLICANT 2813 Art Unit (use as many sheets as necessary) Nguyen, Tuan H. **Examiner Name** of 3 3 Attorney Docket Number Sheet 42390P10254

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7N University, pp. 60-85 (1986).	N	Shacham-Diamand, et al., "0.35 μm Cu-Filled Via Holes by Blanket Deposited Electroless Copper on Sputtered Seed Layer," VMIC Conference, pp. 334-336 (June 1995).	
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	U.S. PATENT DOCUMENTS						
Examiner Initials*	Cite No.1	Document Number  Number - Kind Code <sup>2</sup> (if known)	Publication Date or Issue Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear		
TN		US-4,574,094	03-04-1986	DeLuca et al.			
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TN		US-4,789,648	12-06-1988	Chow et al.	= /		
TN		US-4,894,260	01-16-1990	Kumasaka et al.	<b>-</b> /		
TN		US-4,985,750	01-15-1991	Hoshino	<b>–</b> /		
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	FOREIGN PATENT DOCUMENTS								
Examiner Initials*	Cite No.1	Foreign Patent Document			Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear				
		Country Code <sup>3</sup> - Number <sup>4</sup> - Kind Code <sup>5</sup> (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document					
77/		JP-62[1987]-270778	11-25-1987	Ichiyoshi					
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